

SLF750U

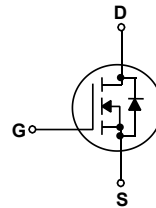
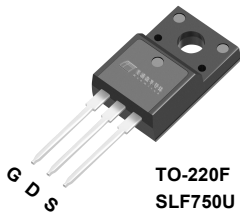
430V N-Channel MOSFET

General Description

This Power MOSFET is produced using Msemitek's advanced planar stripe DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switched mode power supplies, active power factor correction based on half bridge topology.

Features

- N-Channel:430V 11A
 $R_{DS(on)Typ}=0.54\Omega@V_{GS} = 10V$
- Very Low On-resistance RDS(ON)
- LowCrss
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Parameter	SLF750U	Units
V _{DSS}	Drain-Source Voltage	430	V
I _D	Drain Current - Continuous (T _C = 25°C)	11	A
	- Continuous (T _C = 100°C)	6.7	A
I _{DM}	Drain Current - Pulsed (Note 1)	33	A
V _{GSS}	Gate-Source Voltage	±30	V
E _{AS}	Single Pulsed Avalanche Energy	437	mJ
P _D	Power Dissipation (T _C = 25°C)	35	W
R _{θJC}	Thermal Resistance, Junction to Case	3.57	°C/W
T _J , T _{STG}	Operating and Storage Temperature Range	-55 to +150	°C
T _L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	°C

* Drain current limited by maximum junction temperature.

Package Marking

Part Number	Top Marking	Package	Packing Method	MOQ	QTY
SLF750U	SLF750U	TO-220F	Tube	1000	5000

Electrical Characteristics

$T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	430	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 400\text{ V}, V_{GS} = 0\text{ V}$	--	--	1	μA
		$V_{DS} = 340\text{ V}, T_C = 125^\circ\text{C}$	--	--	10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = 30\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = -30\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2	-	4	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = 10\text{ V}, I_D = 5.5\text{ A}$	--	0.54	0.64	Ω

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	835	-	pF
C_{oss}	Output Capacitance		--	98	-	pF
C_{rss}	Reverse Transfer Capacitance		--	3.85	-	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DS} = 210\text{ V},$ $R_G = 25\Omega, I_D = 5.5\text{ A}$	--	19	--	ns
t_r	Turn-On Rise Time		--	70	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	70	--	ns
t_f	Turn-Off Fall Time		--	27	--	ns
Q_g	Total Gate Charge	$V_{DS} = 210\text{ V}, I_D = 5.5\text{ A},$ $V_{GS} = 10\text{ V}$	--	23	--	nC
Q_{gs}	Gate-Source Charge		--	5.4	--	nC
Q_{gd}	Gate-Drain Charge		--	5	--	nC

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain-Source Diode Forward Current	--	--	11	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current	--	--	33	A
V_{SD}	Drain to Source Diode Forward Voltage, $V_{GS} = 0\text{ V}, I_{SD} = 11\text{ A}, T_J = 25^\circ\text{C}$	--	--	1.4	V
t_{rr}	Reverse Recovery Time & $T_J = 25^\circ\text{C}, I_F = 5.5\text{ A di/dt} = 100\text{ A}/\mu\text{s}$	--	410	-	nS
Q_{rr}	Reverse Recovery Charge & $T_J = 25^\circ\text{C}, I_F = 5.5\text{ A di/dt} = 100\text{ A}/\mu\text{s}$	--	7	-	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. EAS condition: $T_J = 25^\circ\text{C}, V_{DD} = 50\text{ V}, V_G = 10\text{ V}, R_G = 25\Omega,$
3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$

N- Channel Typical Characteristics

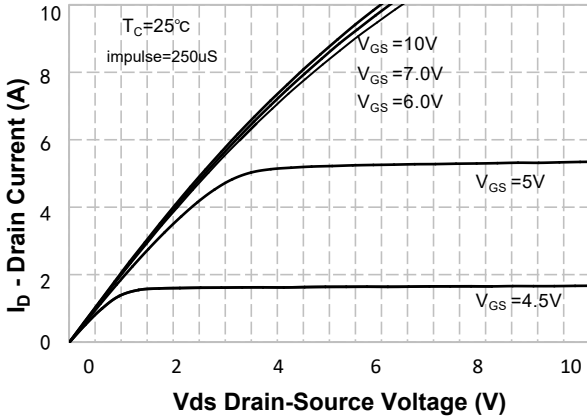


Figure 1. On-Region Characteristics

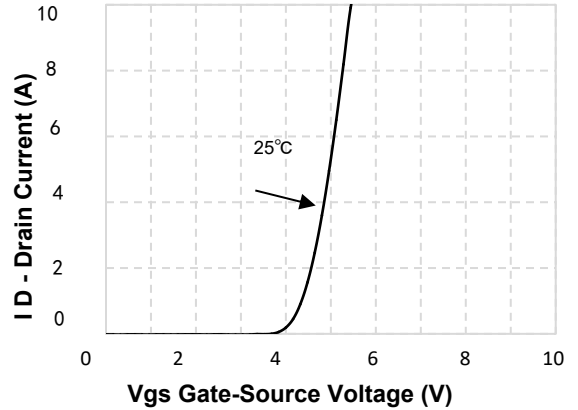


Figure 2. Transfer Characteristics

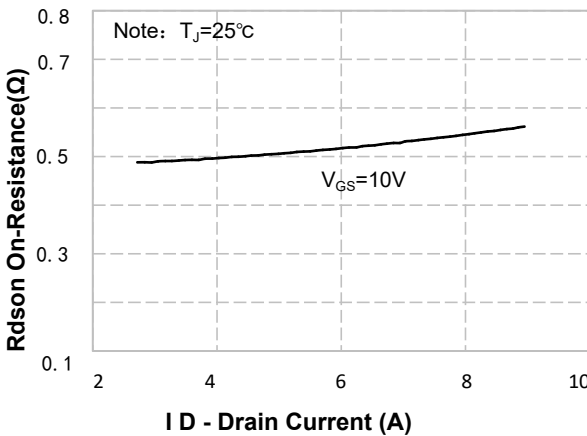


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

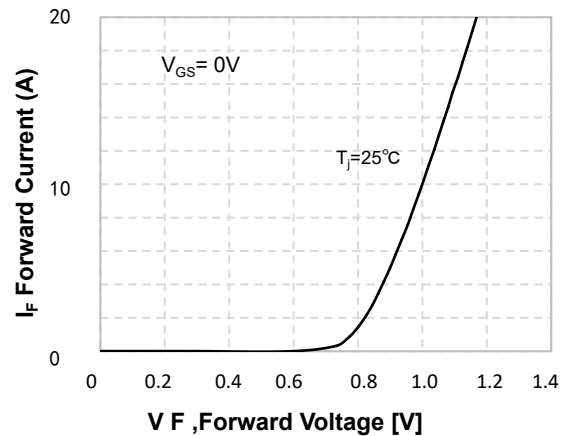


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

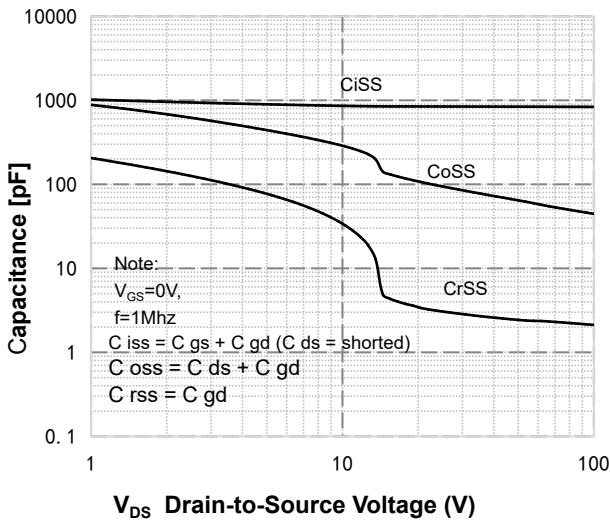


Figure 5. Capacitance Characteristics

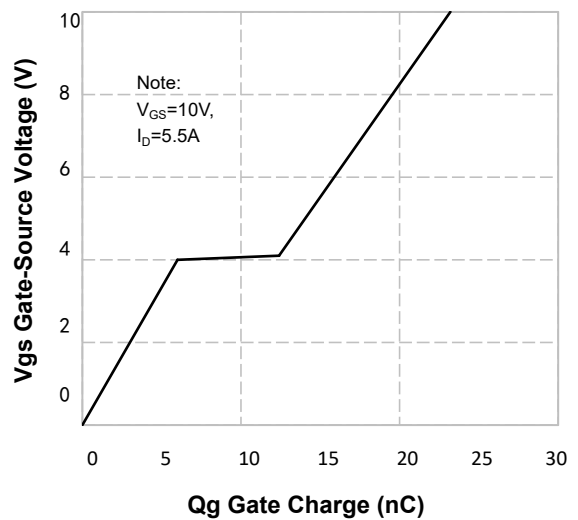


Figure 6. Gate Charge Characteristics

Typical Characteristics (Continued)

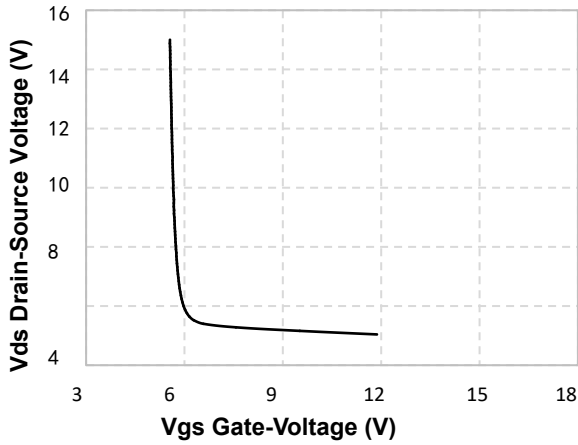


Figure 7. Vds Drain-Source Voltage vs Gate Voltage

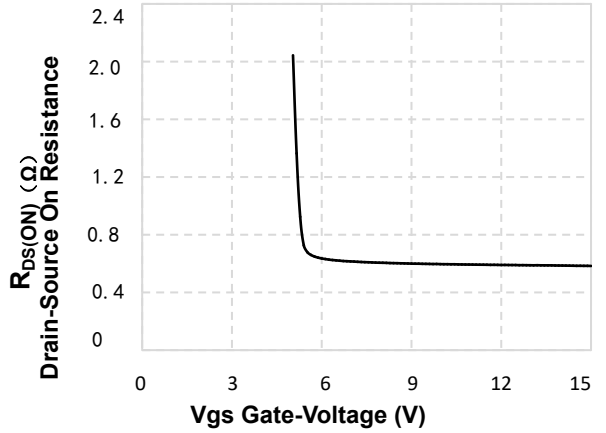


Figure 8. On-Resistance vs Gate Voltage

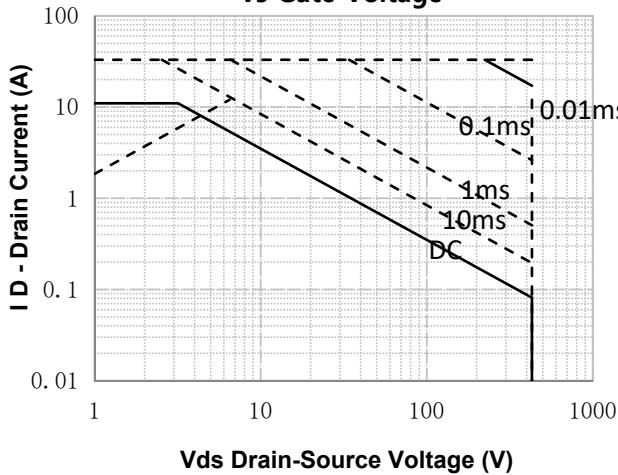


Figure 9. Maximum Safe Operating Area

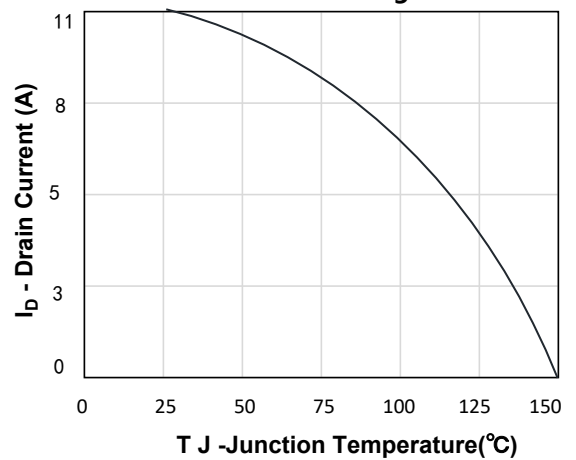


Figure 10. Maximum Drain Current vs Temperature

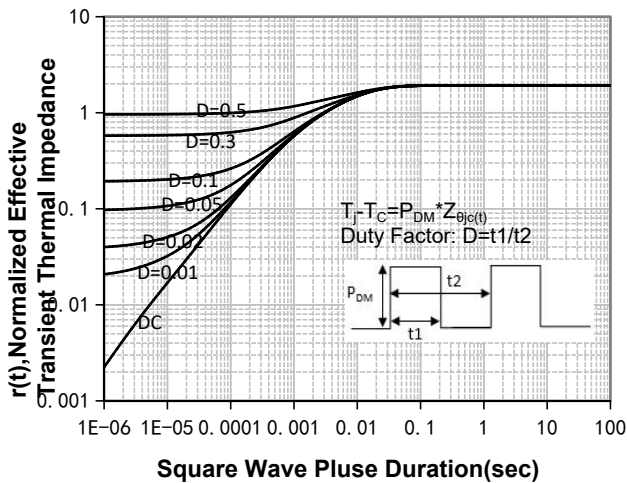
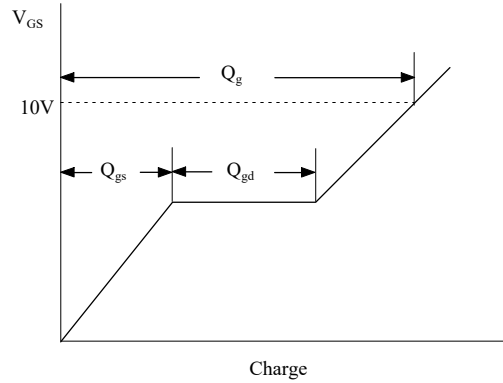
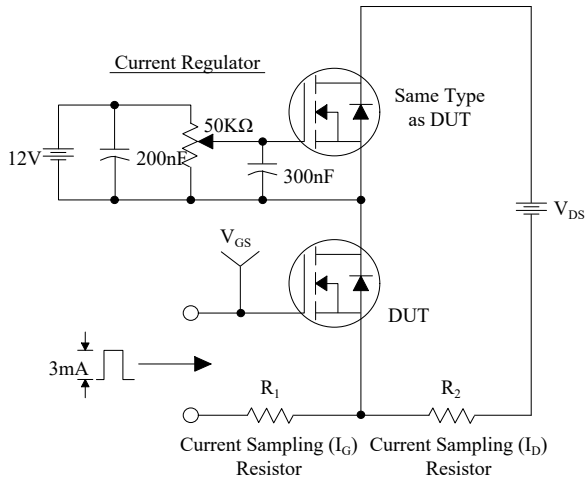
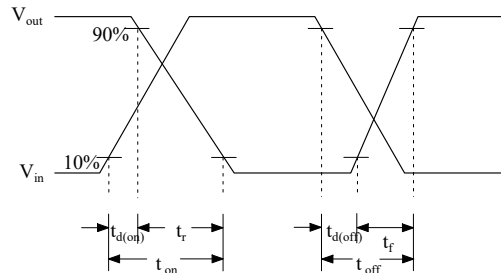
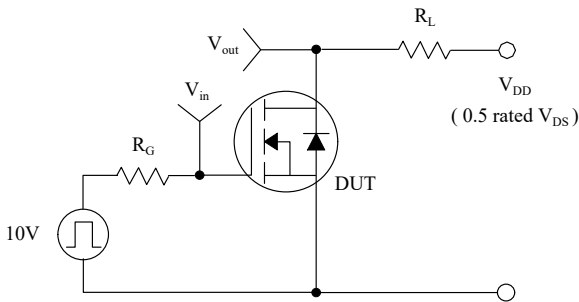


Figure 11. Transient Thermal Response Curve

Gate Charge Test Circuit & Waveform



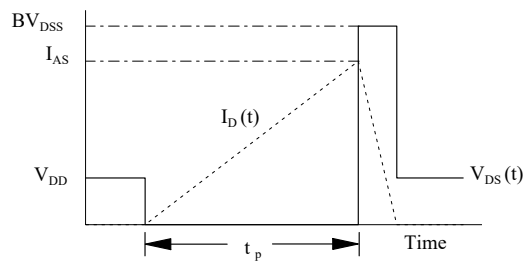
Resistive Switching Test Circuit & Waveforms



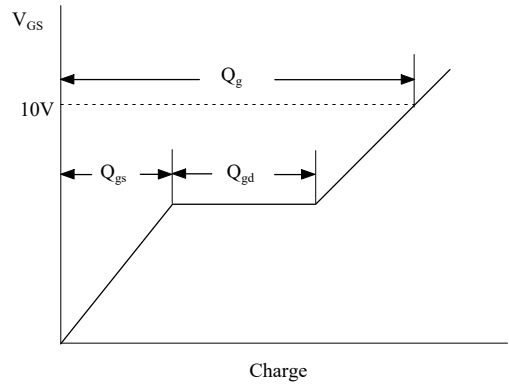
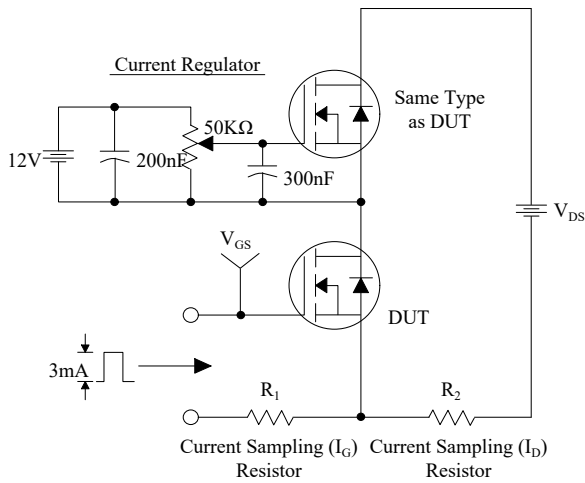
Unclamped Inductive Switching Test Circuit & Waveforms



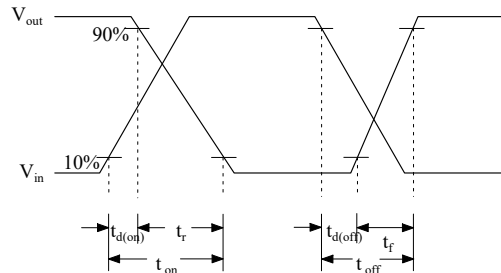
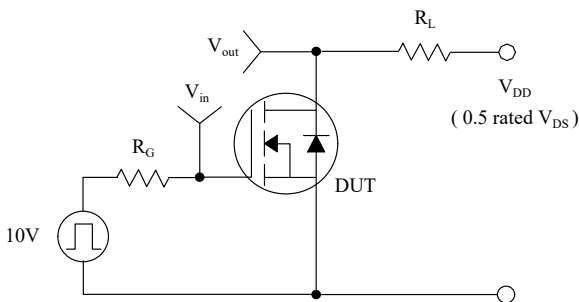
$$E_{AS} = \frac{1}{2} L_L I_{AS}^2$$



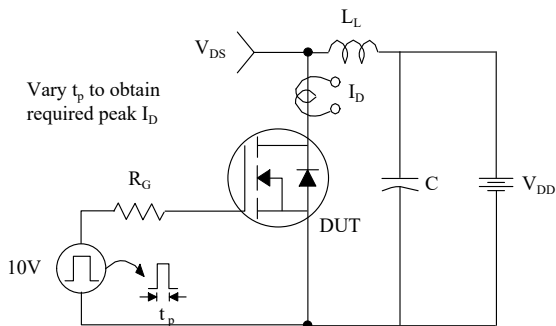
Gate Charge Test Circuit & Waveform



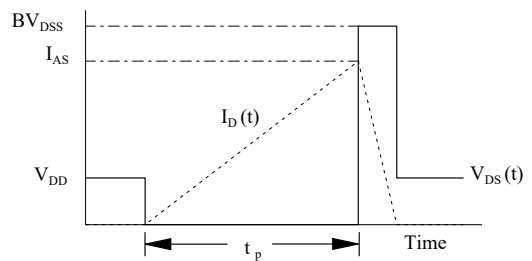
Resistive Switching Test Circuit & Waveforms



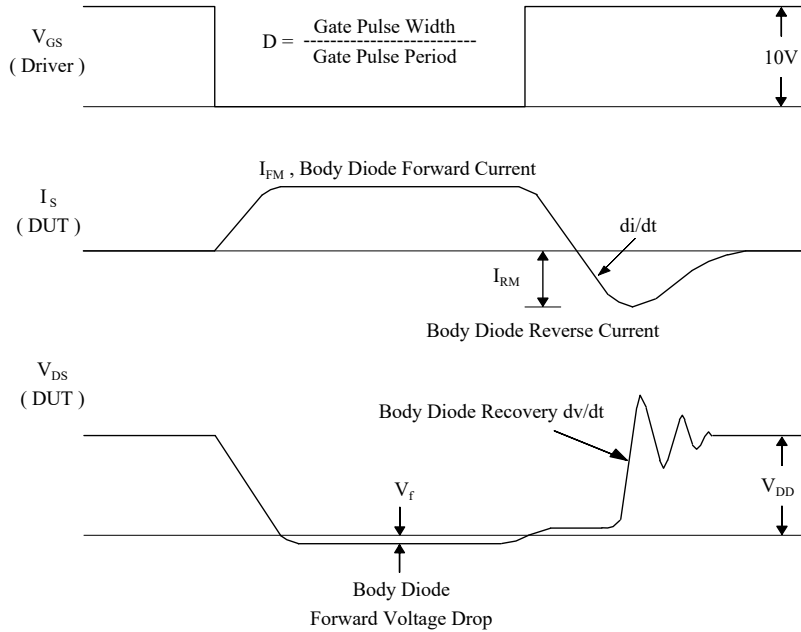
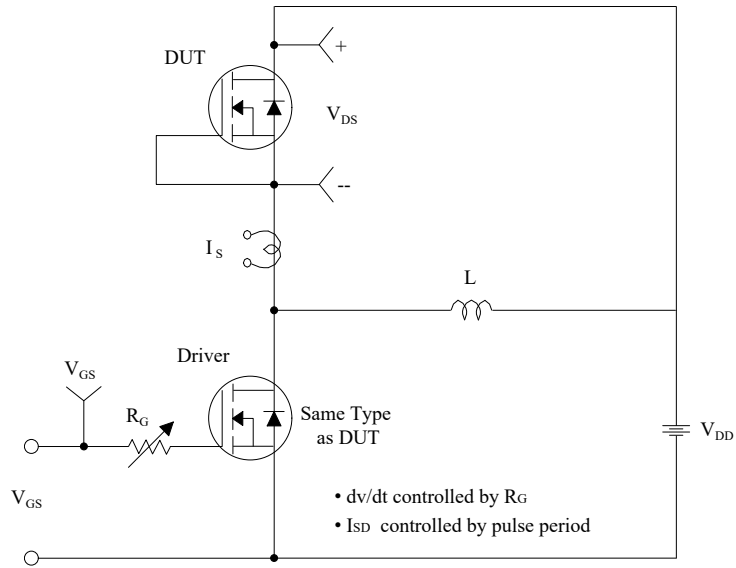
Unclamped Inductive Switching Test Circuit & Waveforms



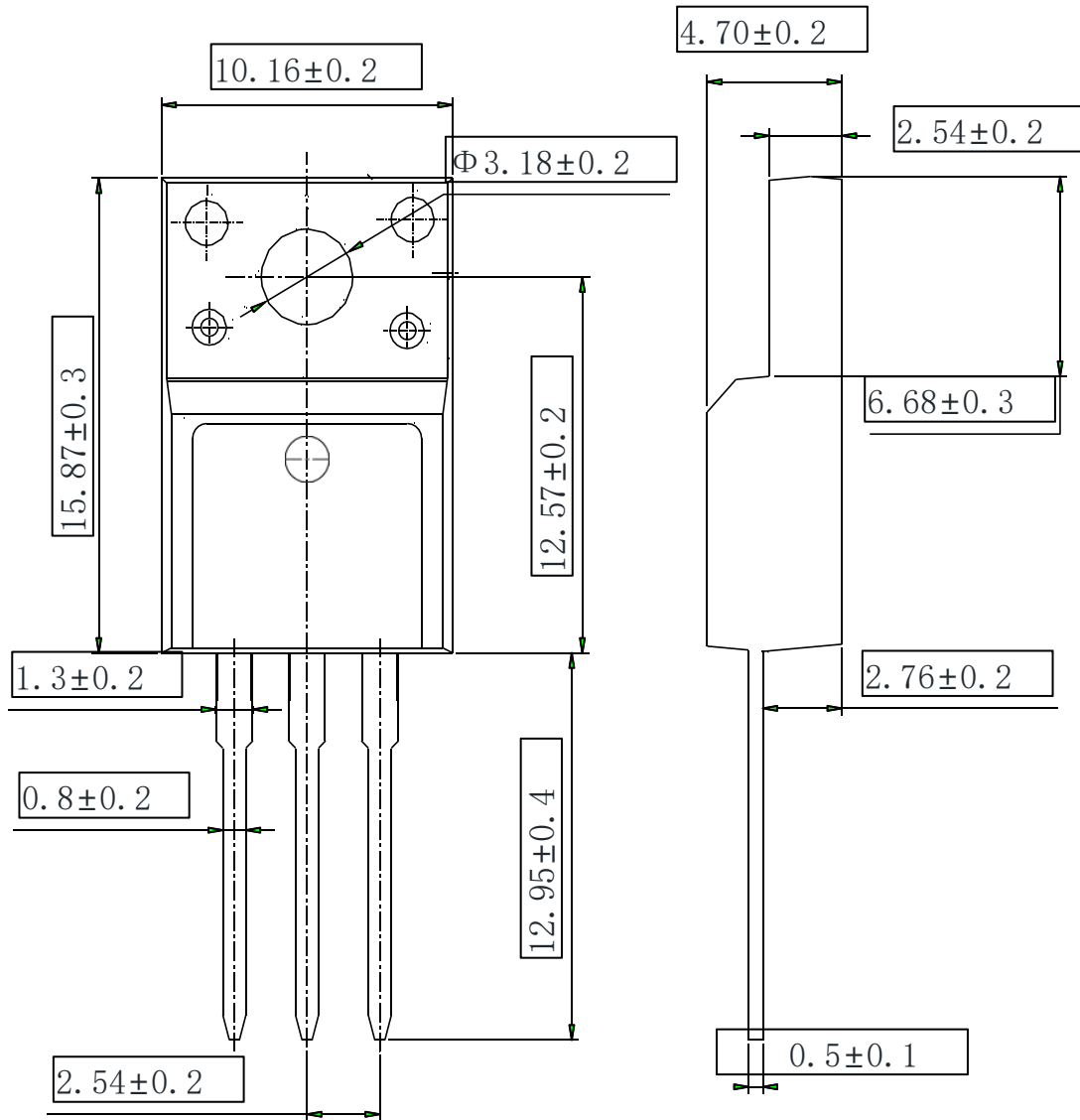
$$E_{AS} = \frac{1}{2} L_L I_{AS}^2$$



Peak Diode Recovery dv/dt Test Circuit & Waveforms



TO-220F OUTLINE



NOTE:

- 1The plastic package is not marked as smooth surface $Ra=0.1$; Subglossy surface $Ra=0.8$
2. Undeclared tolerance ± 0.15 , Unmarked fillet $R_{max}=0.25$

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